



ALPHA & OMEGA
SEMICONDUCTOR



AO4922

Asymmetric Dual N-Channel Enhancement Mode Field Effect Transistor

SRFET™

General Description

The AO4922 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The two MOSFETs make a compact and efficient switch and synchronous rectifier combination for use in DC-DC converters. A monolithically integrated Schottky diode in parallel with the synchronous MOSFET to boost efficiency further. *Standard Product AO4922 is Pb-free (meets ROHS & Sony 259 specifications). AO4922L is a Green Product ordering option. AO4922L and AO4922 are electrically identical.*

Features

FET1

$V_{DS}(V) = 30V$

$I_D = 9A$

$R_{DS(ON)} < 15.8m\Omega$

$R_{DS(ON)} < 18.5m\Omega$

FET2

$V_{DS}(V) = 30V$

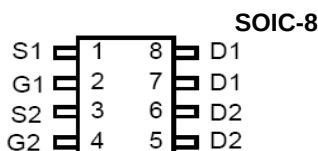
$I_D = 7.3A$ ($V_{GS} = 10V$)

$< 24m\Omega$ ($V_{GS} = 10V$)

$< 29m\Omega$ ($V_{GS} = 4.5V$)

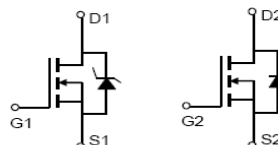
UIS TESTED!

Rg, Ciss, Coss, Crss Tested



SRFET™

Soft Recovery MOSFET:
Integrated Schottky Diode



Absolute Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Max FET1	Max FET2	Units
Drain-Source Voltage	V_{DS}	30	30	V
Gate-Source Voltage	V_{GS}	± 12	± 12	V
Continuous Drain Current ^A	I_{DSM}	9.0	7.3	A
$T_A = 25^\circ C$				
$T_A = 70^\circ C$		7.2	5.9	
Pulsed Drain Current ^B	I_{DM}	40	40	
Avalanche Current ^B	I_{AR}	22	12	A
Repetitive avalanche energy $L = 0.3mH$ ^B	E_{AR}	73	22	mJ
Power Dissipation ^A	P_{DSM}	2.0	2.0	W
		1.3	1.3	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Thermal Characteristics FET1

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	48	62.5	$^\circ C/W$
$t \leq 10s$				
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	74	90	$^\circ C/W$
Steady-State				
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	32	40	$^\circ C/W$

Thermal Characteristics FET2

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	48	62.5	$^\circ C/W$
$t \leq 10s$				
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	74	90	$^\circ C/W$
Steady-State				
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	32	40	$^\circ C/W$

FET1 Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ $T_J=125^{\circ}\text{C}$		0.01 6	0.1 20	mA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			0.1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.5	1.8	2.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=9\text{A}$ $T_J=125^{\circ}\text{C}$		13 20.2	15.8 25.2	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=7\text{A}$		15	18.5	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=9\text{A}$		78		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.38	0.5	V
I_S	Maximum Body-Diode + Schottky Continuous Current				4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		1980	2574	pF
C_{oss}	Output Capacitance			317		pF
C_{rss}	Reverse Transfer Capacitance			111		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.3	2.0	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=9\text{A}$		33.0	43	
$Q_g(4.5\text{V})$	Total Gate Charge			15.0		nC
Q_{gs}	Gate Source Charge			5.3		nC
Q_{gd}	Gate Drain Charge			6.0		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=1.7\Omega$, $R_{GEN}=3\Omega$		5.5		ns
t_r	Turn-On Rise Time			5.5		ns
$t_{D(off)}$	Turn-Off DelayTime			27.0		ns
t_f	Turn-Off Fall Time			4.3		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=9\text{A}$, $dI/dt=300\text{A}/\mu\text{s}$		11	13	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=9\text{A}$, $dI/dt=300\text{A}/\mu\text{s}$		7		nC

A: The value of $R_{\theta JA}$ is measured with the device in a still air environment with $T_A=25^{\circ}\text{C}$. The power dissipation P_{DSM} and current rating I_{DSM} are based on $T_{J(MAX)}=150^{\circ}\text{C}$, using $t \leq 10\text{s}$ junction-to-ambient thermal resistance.

B: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

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FET1 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

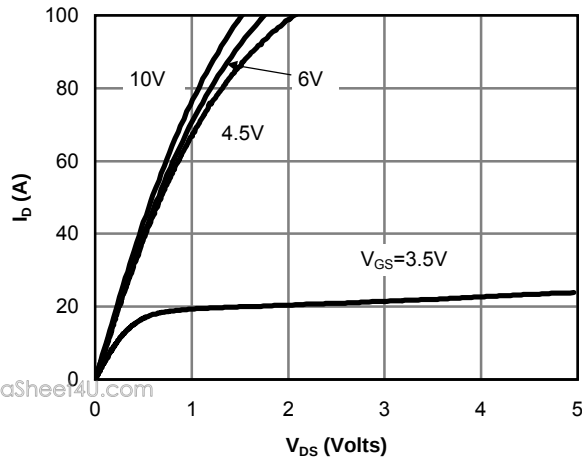


Figure 1: On-Region Characteristics

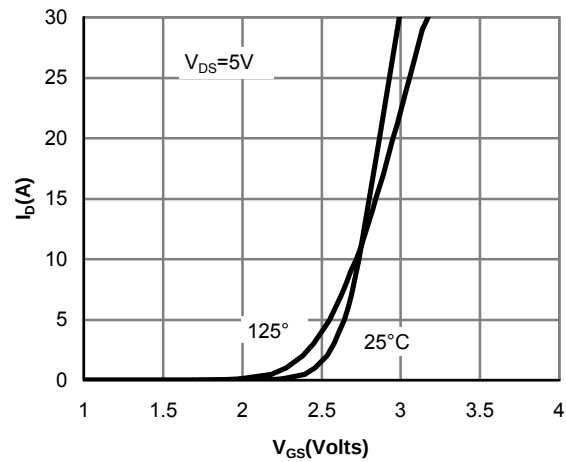


Figure 2: Transfer Characteristics

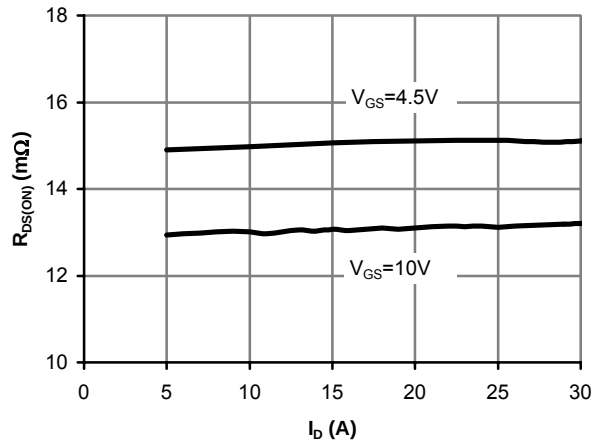


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

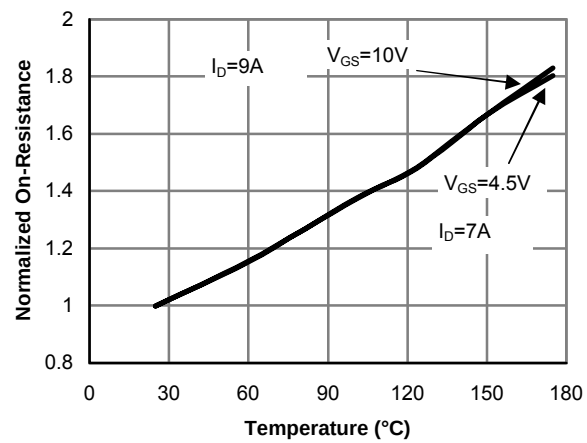


Figure 4: On-Resistance vs. Junction Temperature

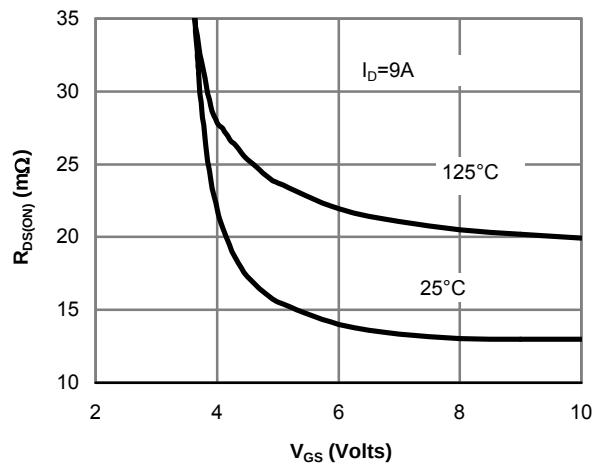


Figure 5: On-Resistance vs. Gate-Source Voltage

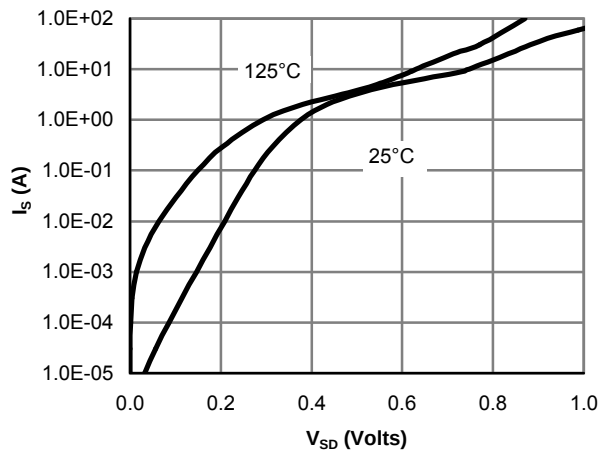


Figure 6: Body-Diode Characteristics

FET1 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

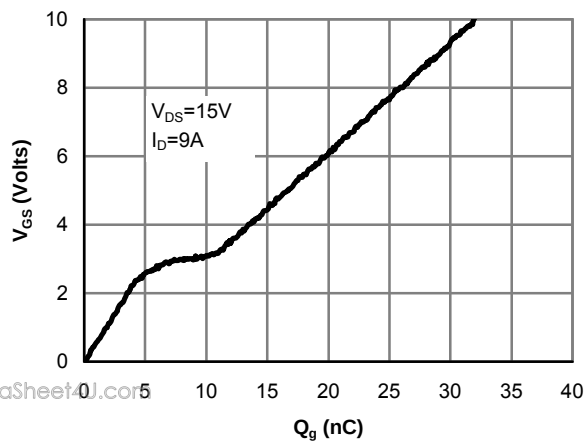


Figure 7: Gate-Charge Characteristics

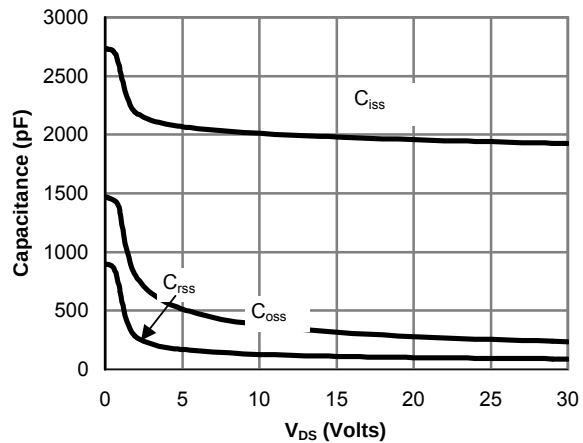


Figure 8: Capacitance Characteristics

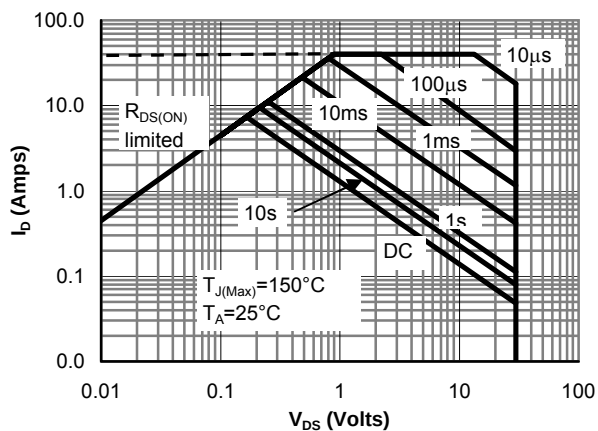


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

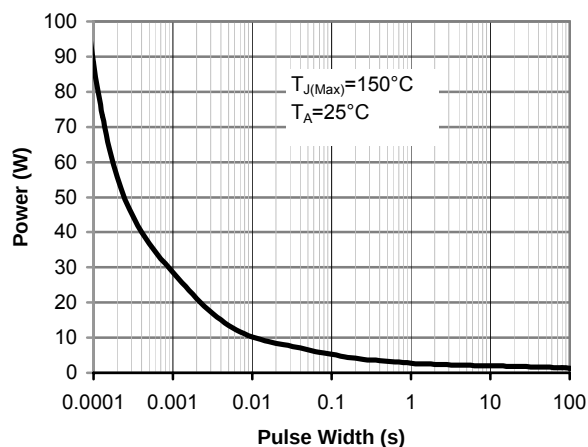


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

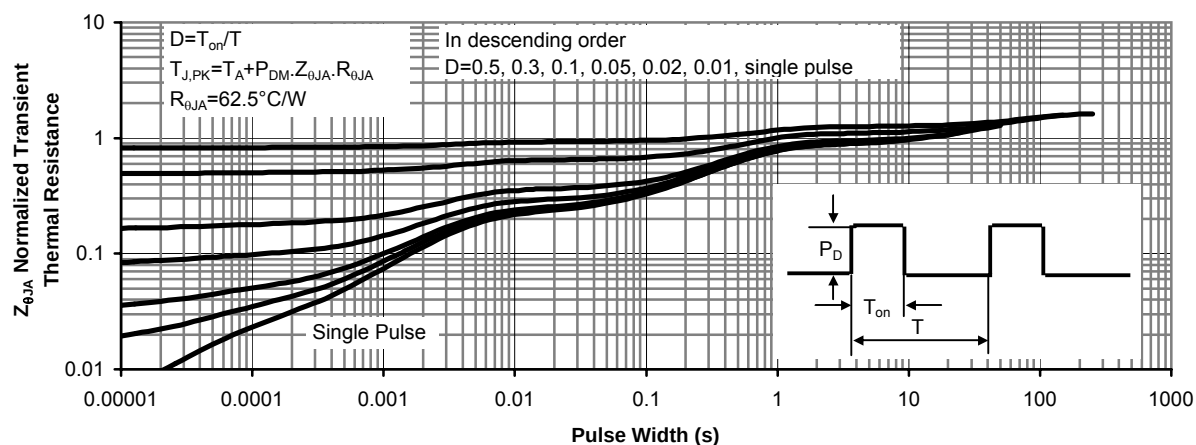


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

FET1 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

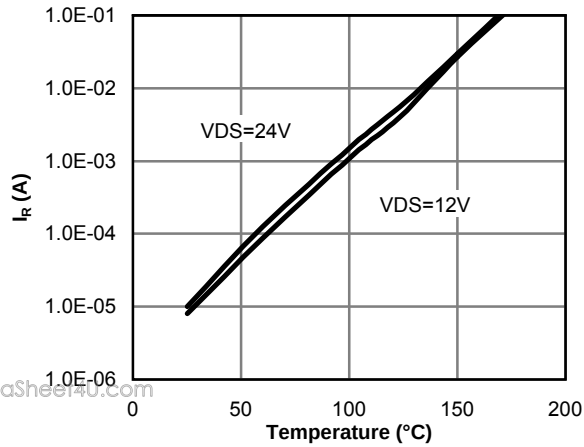


Figure 12: Diode Reverse Leakage Current vs. Junction Temperature

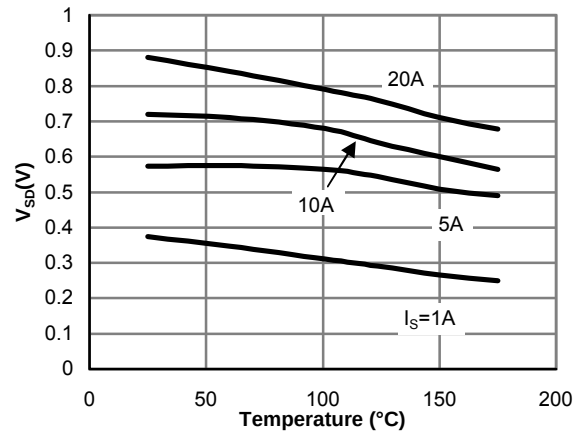


Figure 13: Diode Forward voltage vs. Junction Temperature

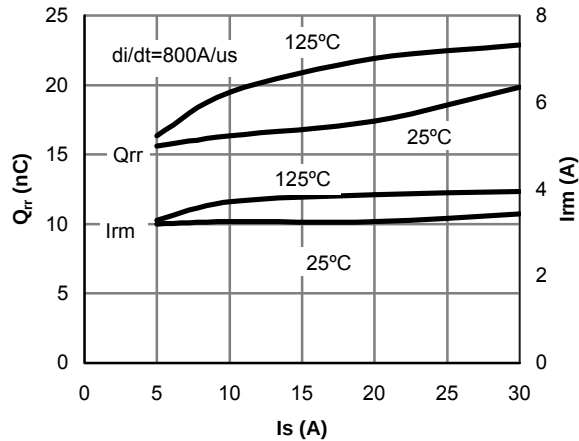


Figure 14: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current

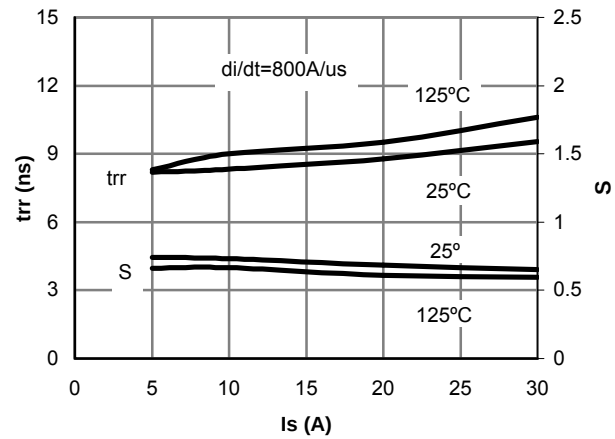


Figure 15: Diode Reverse Recovery Time and Soft Coefficient vs. Conduction Current

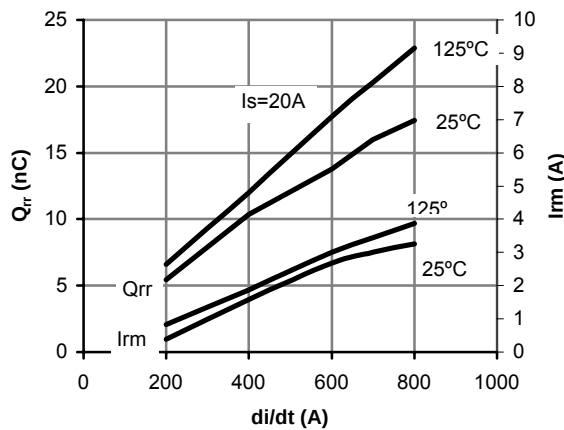


Figure 16: Diode Reverse Recovery Charge and Peak Current vs. di/dt

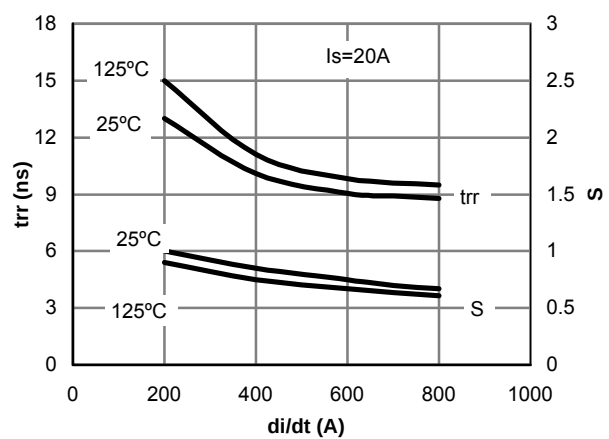


Figure 17: Diode Reverse Recovery Time and Soft Coefficient vs. di/dt

FET2 Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$		0.002	1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.7	1	1.5	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=7.3\text{A}$ $T_J=125^{\circ}\text{C}$		20 28	24 35	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=6\text{A}$		23.5	29	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$, $I_D=5\text{A}$		34.7	48	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=7.3\text{A}$		26		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.71	1	V
I_S	Maximum Body-Diode Continuous Current				2.8	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		900	1100	pF
C_{oss}	Output Capacitance			88		pF
C_{rss}	Reverse Transfer Capacitance			65		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		0.95	1.5	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=4.5\text{V}$, $V_{DS}=15\text{V}$, $I_D=7.3\text{A}$		10	12	nC
Q_{gs}	Gate Source Charge			1.8		nC
Q_{gd}	Gate Drain Charge			3.75		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=2\Omega$, $R_{GEN}=6\Omega$		3.2		ns
t_r	Turn-On Rise Time			3.5		ns
$t_{D(off)}$	Turn-Off DelayTime			21.5		ns
t_f	Turn-Off Fall Time			2.7		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=7.3\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		16.8	21	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=7.3\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		8		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t_s \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

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FET2 TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

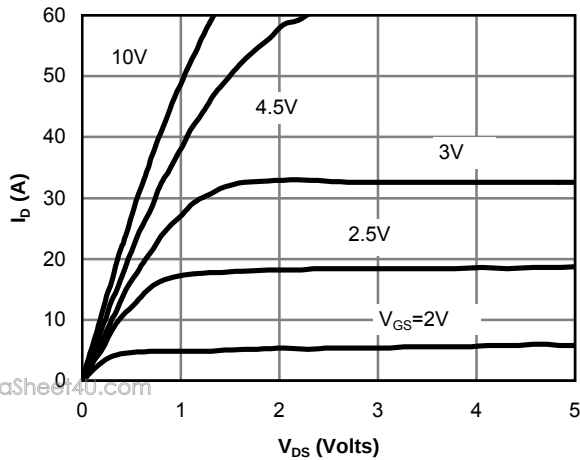


Figure 1: On-Region Characteristics

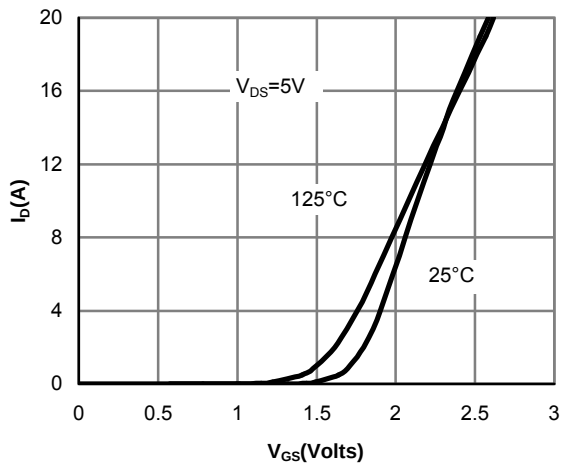


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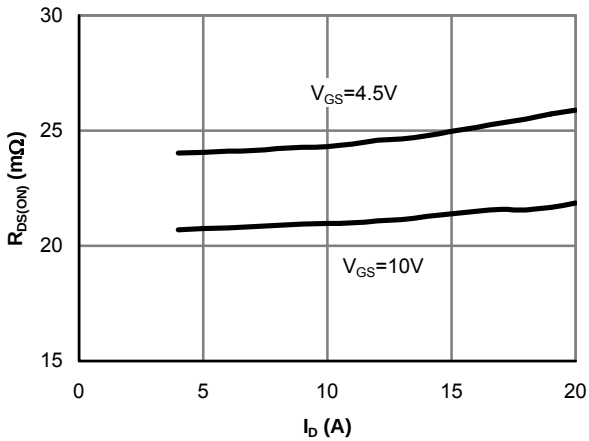


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

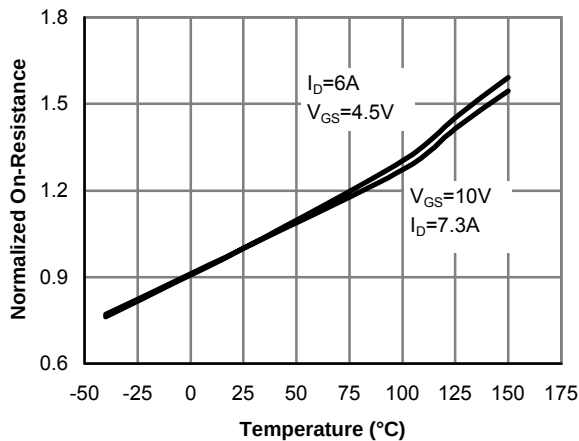


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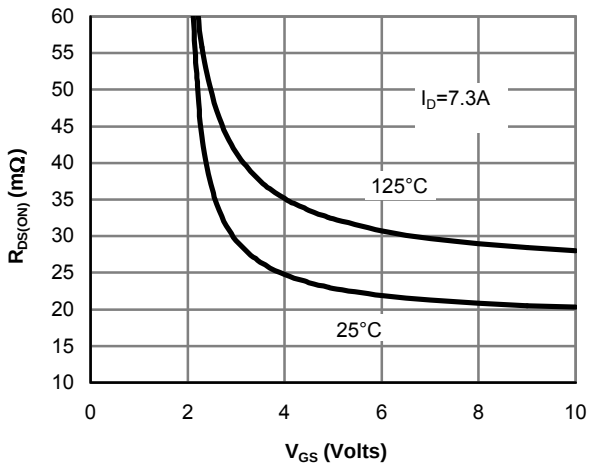


Figure 5: On-Resistance vs. Gate-Source Voltage

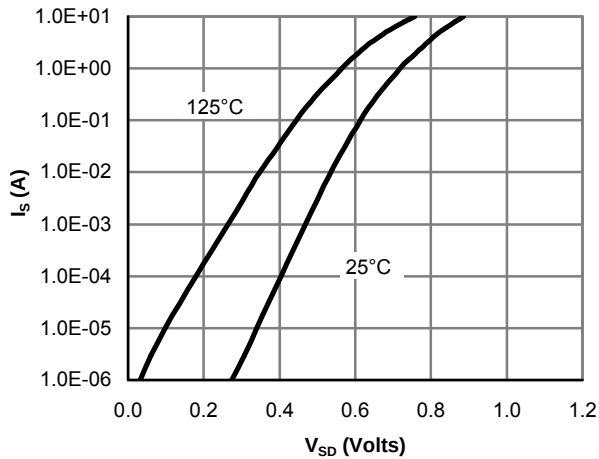


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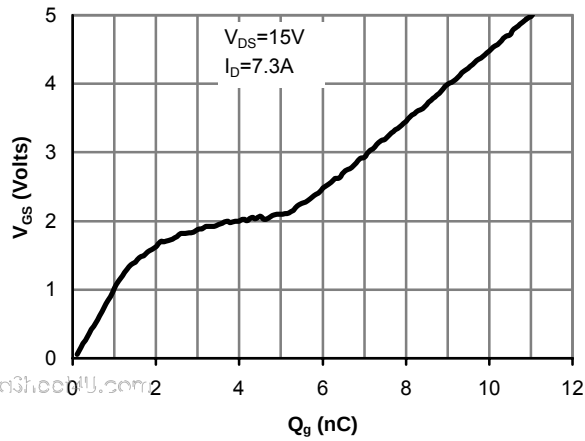


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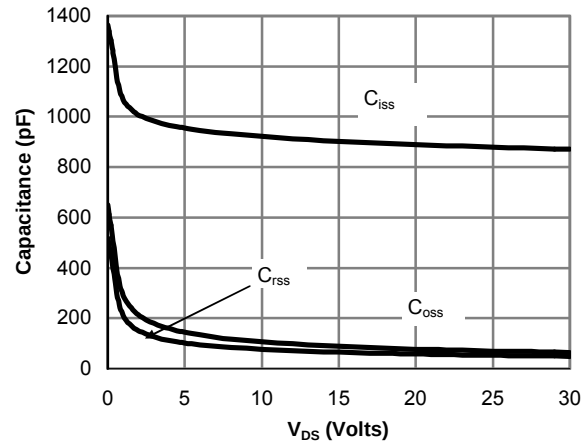


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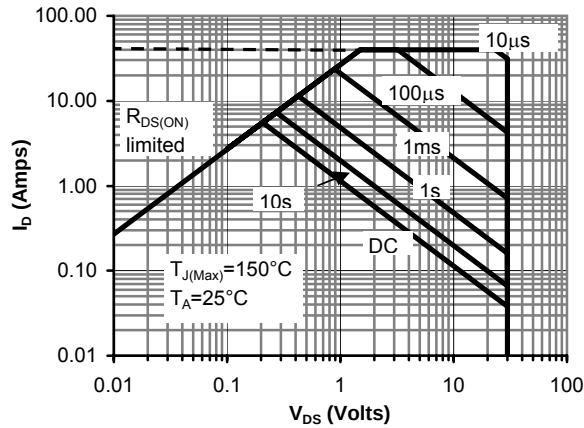


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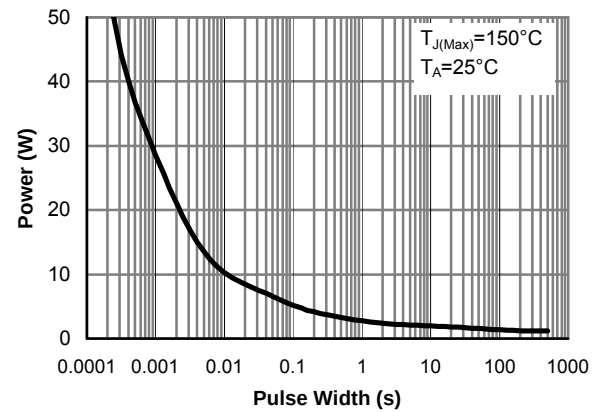


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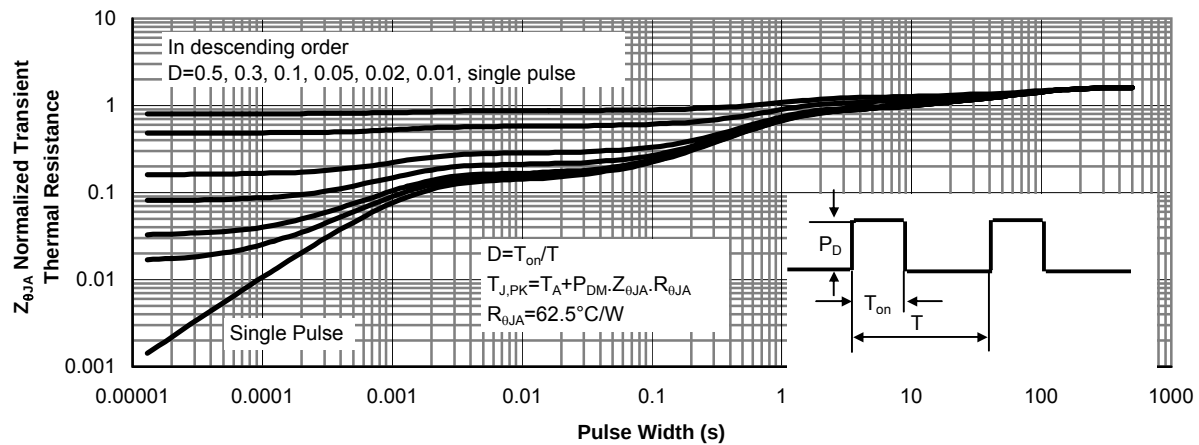


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